

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Amended) A semiconductor device comprising:
a source, a gate and a drain;
a source-drain depletion region in a substrate under the gate;
a single deep-pocket ion implant in the source-drain depletion region at a drain side; and
a single shallow-pocket ion implant in the source-drain depletion region at a source side.
2. - 14. (Canceled)
15. (Amended) The semiconductor device as recited in claim 1[[0]], further comprising:
a secondary deep-pocket ion implant in a source side of the source-drain depletion region,
the secondary deep-pocket ion implant having been countered by ions of the source; and
a secondary shallow-pocket ion implant in a drain side of the source-drain depletion region,
the secondary shallow-pocket ion implant having been countered by ions of the drain.
16. (Amended) The semiconductor device as recited in claim [[1]] 22, further comprising:
a secondary deep-pocket ion implant in a drain side of the source-drain depletion region,
the secondary deep-pocket ion implant having been countered by ions of the drain; and
a secondary shallow-pocket ion implant in a source side of the source-drain depletion region,
the secondary shallow-pocket ion implant having been countered by ions of the source.
17. - 21. (Canceled)
22. (New) A semiconductor device comprising:
a source, a gate and a drain;
a source-drain depletion region in a substrate under the gate;

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a single deep-pocket ion implant in the source-drain depletion region at a source side; and
a single shallow-pocket ion implant in the source-drain depletion region at a drain side.